

P-Channel 8-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
- 8	0.122 at V _{GS} = - 4.5 V	1.2	5.91
	0.141 at V _{GS} = - 2.5 V	1.1	
	0.168 at V _{GS} = - 1.8 V	0.60	
	0.198 at V _{GS} = - 1.5 V	0.50	

FEATURES

- Halogen-free Option Available
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested

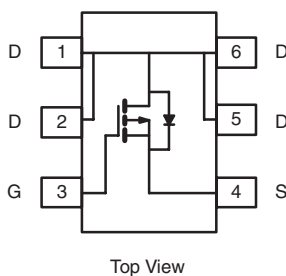


RoHS
COMPLIANT

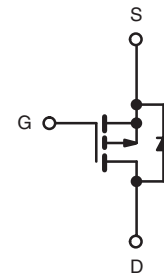
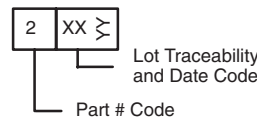
APPLICATIONS

- Load Switch for Portable Applications

SC-89 (6-LEADS)



Marking Code



Ordering Information: Si1051X-T1-E3 (Lead (Pb)-free)
Si1051X-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 8	V
Gate-Source Voltage	V _{GS}	± 5	
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	1.2 ^{b, c}
		T _A = 70 °C	0.97 ^{b, c}
Pulsed Drain Current	I _{DM}	- 8	A
Continuous Source-Drain Diode Current	I _S	0.2 ^{b, c}	A
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	0.236 ^{b, c}
		T _A = 70 °C	0.151 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	R _{thJA}	t ≤ 5 s	440	530	°C/W
		Steady State	540	650	

Notes:

- Based on T_A = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under Steady State conditions is 650 °C/W.

Si1051X

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SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 6.19		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.13		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.3		- 1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$			- 1	nA
		$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			- 10	μA
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = -4.5\text{ V}$	- 8			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1.2\text{ A}$		0.091	0.122	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -1.1\text{ A}$		0.106	0.141	
		$V_{GS} = -1.8\text{ V}, I_D = -0.60\text{ A}$		0.117	0.168	
		$V_{GS} = -1.5\text{ V}, I_D = -0.50\text{ A}$		0.129	0.198	
Forward Transconductance	g_{fs}	$V_{DS} = -4\text{ V}, I_D = -1.2\text{ A}$		4.93		S
Dynamic^b						
Input Capacitance	C_{ISS}	$V_{DS} = -4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		560		pF
Output Capacitance	C_{OSS}			180		
Reverse Transfer Capacitance	C_{RSS}			112		
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}, V_{GS} = -5\text{ V}, I_D = -1.2\text{ A}$		6.3	9.45	nC
				5.91	8.87	
Gate-Source Charge	Q_{gs}	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.2\text{ A}$		1.98		
Gate-Drain Charge	Q_{gd}			1.25		
Gate Resistance	R_g	$f = 1\text{ MHz}$		9.8	14.7	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 4.16\text{ }\Omega$ $I_D \cong -0.96\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		7.2	10.8	ns
Rise Time	t_r			36	54	
Turn-Off Delay Time	$t_{d(off)}$			52	78	
Fall Time	t_f			16	24	
Drain-Source Body Diode Characteristics						
Pulse Diode Forward Current ^a	I_{SM}				- 8	A
Body Diode Voltage	V_{SD}	$I_S = -1.0\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		18.8	28.2	nC
Body Diode Reverse Recovery Charge	Q_{rr}			4.7	7.05	ns
Reverse Recovery Fall Time	t_a			15		
Reverse Recovery Rise Time	t_b			3.8		

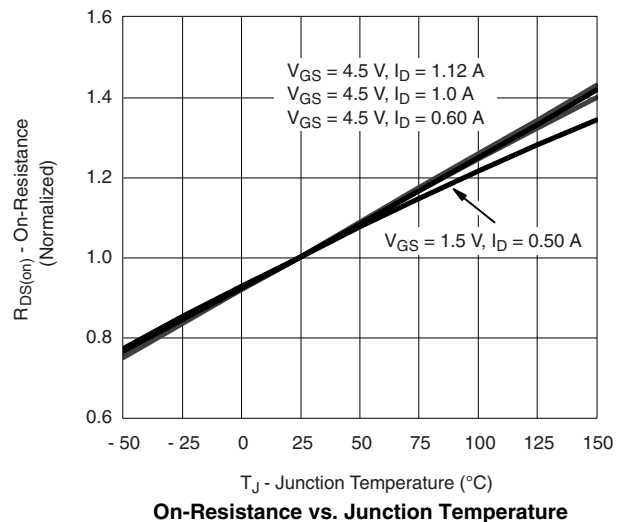
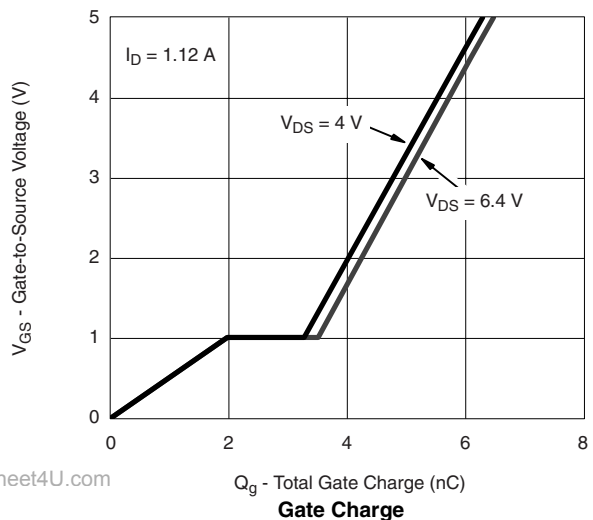
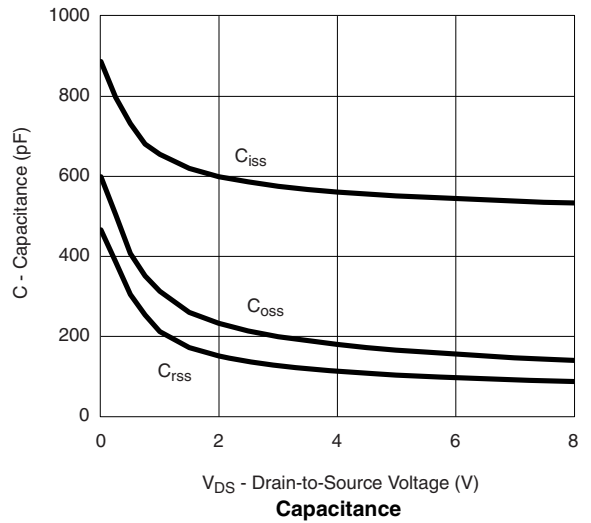
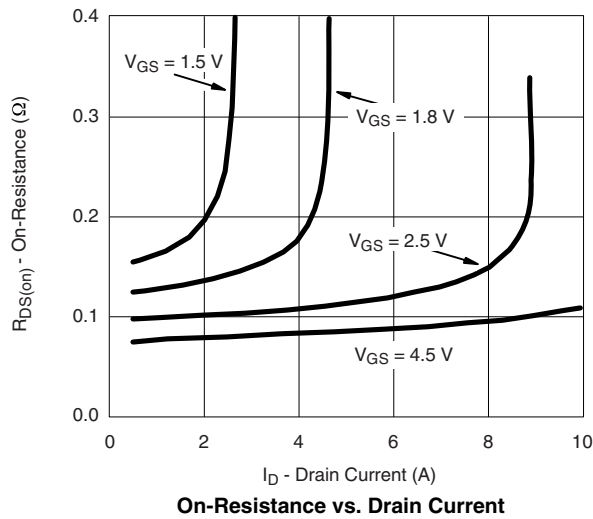
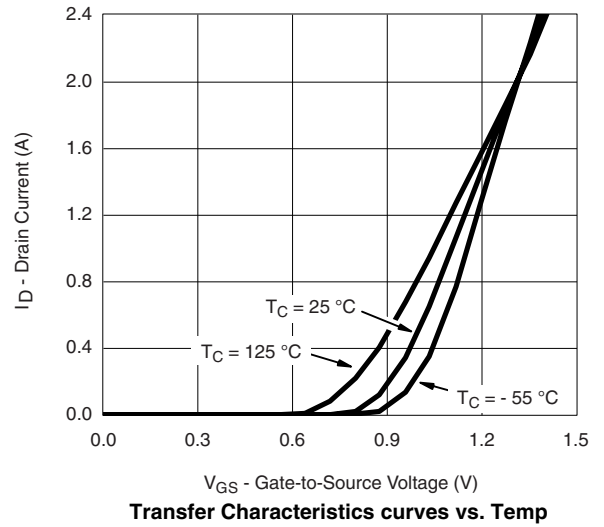
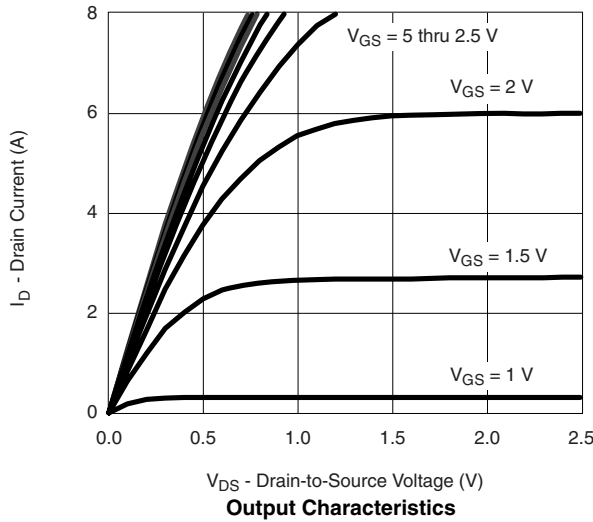
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted

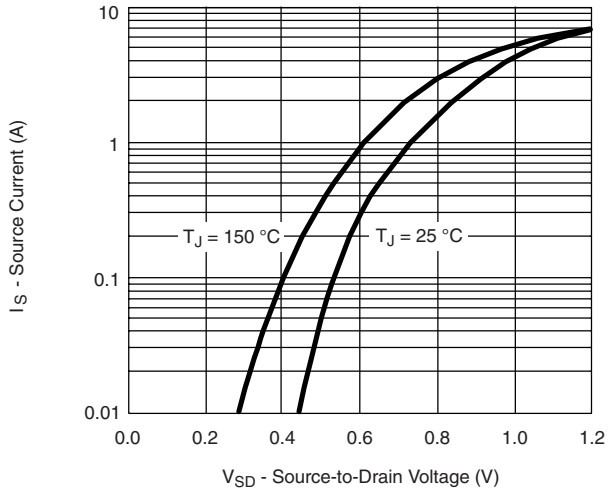


Si1051X

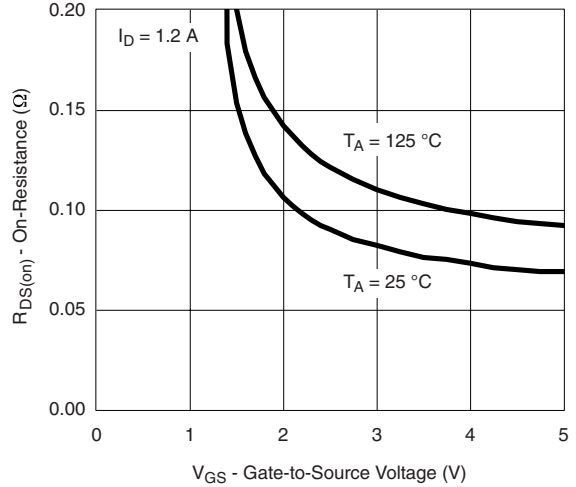


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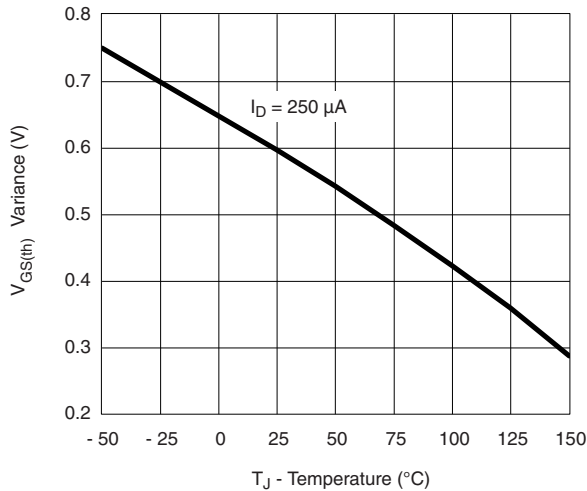
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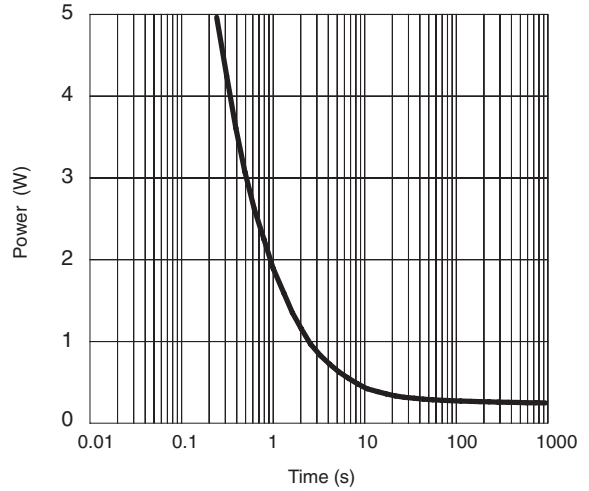
Source-Drain Diode Forward Voltage



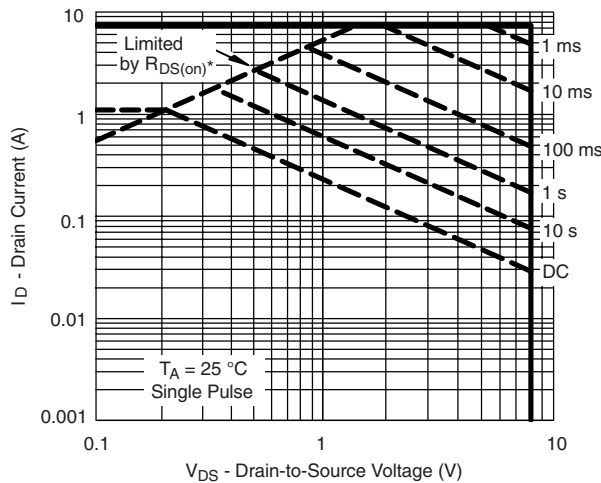
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power

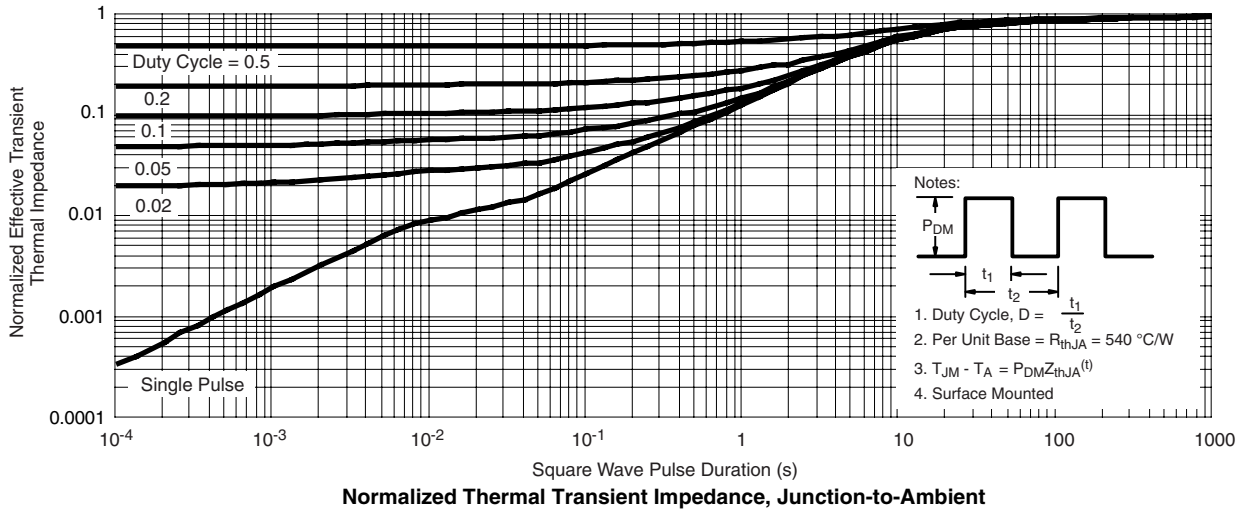


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient



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